

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	27	semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:45
L7	61	(438/422,411,632,619,618,631, 622.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:46
L8	61	(438/422,411,632,619,618,631, 622.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:53
S1	376	(438/618).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:46
S2	191	(438/619).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:36
S3	529	(438/622).CCLS.	USPAT; USOCR	OR	OFF	2005/10/20 07:31
S4	399	(438/631).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 13:54
S5	126	(438/632).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:27
S6	70	(438/411).CCLS.	USPAT; USOCR	OR	OFF	2006/01/28 13:48
S7	143	(438/421).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 12:01
S8	61	(438/422).CCLS.	USPAT; USOCR	OR	OFF	2001/09/10 11:34
S9	20	(257/527).CCLS.	USPAT; USOCR	OR	OFF	2006/01/30 19:30
S11	42317	"438"/\$.ccls.	USPAT	OR	OFF	2001/09/10 14:19
S14	52856	"257"/\$.ccls.	USPAT	OR	OFF	2005/04/04 13:08
S15	0	"438"/\$.ccls. with (air adj gap) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S16	0	"257"/\$.ccls. with (air adj gap) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S17	0	("257"/\$.ccls. same (air adj gap)) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10
S18	0	("438"/\$.ccls. same (air adj gap)) and @ad<="20000724"	USPAT	OR	OFF	2005/04/04 13:10

S19	0	("438"/\$.ccls. with (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S20	0	("257"/\$.ccls. with (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S21	0	("257"/\$.ccls. same (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S22	0	("438"/\$.ccls. same (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:11
S23	484	("438"/\$.ccls. and (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:13
S24	4075	(semiconductor and (air adj gap)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:12
S25	544	(semiconductor and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:12
S26	157	("438"/\$.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:17
S27	241	("257"/\$.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/04/04 13:47
S28	61	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:53

S29	2	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:46
S30	136	(438/411).CCLS.	USPAT; USOCR	OR	OFF	2005/10/20 07:31
S31	2	(438/422,411,632,619,618,631,622.ccls. and (air adj gap)) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/28 13:47
S32	27	semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD")) and @ad<="20000724"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/30 19:45
S33	0	(semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD"))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/01/28 13:46
S34	0	(semiconductor and (air adj gap) and (metal adj (layer or film)) and ((atmospheric adj pressure adj chemical adj vapor adj deposition) or ("APCVD"))).clm.	US-PGPUB	OR	OFF	2006/01/28 13:46
S35	30	(257/527).CCLS.	USPAT; USOCR	OR	OFF	2006/01/28 13:47
S36	172	(438/411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:48
S37	392	(438/421).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:49
S38	180	(438/359).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:49

S39	897	(438/404).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:49
S40	250	(438/456).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:50
S41	414	(438/619).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 13:50